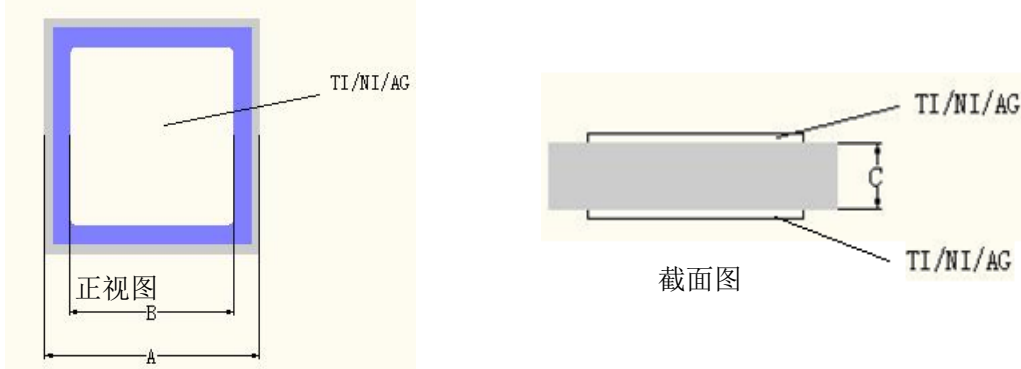


TVS 芯片（平面低压系列产品）

一、芯片特征：

1. 平面工艺
2. 超低反向漏电
3. 芯片表面两面蒸镀Ti/Ni/Ag

二、芯片结构



三、产品型号及规格：

1. 200W

Part Number		Dice Scale (A)	Scale (B)	Scale (C)	Reverse stand-off Voltage	Breakdown voltage		Test Current	Reverse Leakage		Max Clamp Voltage	Peak Pulse Current
						VBR@IT			IR@VRWM			
						VRWM	Min	Max	IT	UNI	BI	
UNI	BI	mil	mil	um	V	V	V	mA	uA	uA	V	A
SMFJ5.0A	SMFJ5.0CA	47±2	35±1	320±20	5.0	6.40	7.07	10	100	100	9.2	21.7
SMFJ6.0A	SMFJ6.0CA	47±2	35±1	320±20	6.0	6.67	7.37	10	100	100	10.3	19.4
/	SMFJ6.5CA	47±2	35±1	320±20	6.5	7.22	7.98	10	100	100	11.2	17.9
P2KE6.8A	P2KE6.8CA	47±2	35±1	320±20	5.8	6.45	7.14	10	100	100	10.5	19.0
/	P2KE7.5CA	47±2	35±1	320±20	6.4	7.13	7.88	10	100	100	11.3	17.6

2. 400W

Part Number		Dice Scale (A)	Scale (B)	Scale (C)	Reverse stand-off Voltage	Breakdown voltage		Test Current	Reverse Leakage		Max Clamp Voltage	Peak Pulse Current
						VBR@IT			IR@VRWM			
						VRWM	Min	Max	IT	UNI	BI	
UNI	BI	UNI/BI	UNI/BI	um	V	V	V	mA	uA	uA	V	A
SMAJ5.0A	SMAJ5.0CA	60±2/70±2	48±1/58±1	320±20	5.0	6.40	7.07	10	100	100	9.2	43.5
SMAJ6.0A	SMAJ6.0CA	60±2/70±2	48±1/58±1	320±20	6.0	6.67	7.37	10	100	100	10.3	38.8
/	SMAJ6.5CA	60±2	48±1	320±20	6.5	7.22	7.98	10	100	100	11.2	35.7
P4KE6.8A	P4KE6.8CA	60±2/70±2	48±1/58±1	320±20	5.8	6.45	7.14	10	100	100	10.5	38.1
/	P4KE7.5CA	60±2	48±1	320±20	6.4	7.13	7.88	10	100	100	11.3	36.3

## 3. 600W

Part Number		Dice Scale (A)	Scale (B)	Scale (C)	Reverse stand-off Voltage	Breakdown voltage		Test Current	Reverse Leakage		Max Clamp Voltage	Peak Pulse Current
						VBR@IT			IR@VRWM			
						VRWM	Min	Max	IT	UNI	BI	V
UNI	BI	mil	mil	um	V	V	V	mA	uA	uA	V	A
SMBJ5.0A	SMBJ5.0CA	79±2	64±1	320±20	5.0	6.40	7.07	10	100	100	9.2	65.2
SMBJ6.0A	SMBJ6.0CA	79±2	64±1	320±20	6.0	6.67	7.37	10	100	100	10.3	58.3
/	SMBJ6.5CA	79±2	64±1	320±20	6.5	7.22	7.98	10	100	100	11.2	53.6
P6KE6.8A	P6KE6.8CA	79±2	64±1	320±20	5.8	6.45	7.14	10	100	100	10.5	57.1
/	P6KE7.5CA	79±2	64±1	320±20	6.4	7.13	7.88	10	100	100	11.3	54.0